Preferred Device

## 24 and 40 Watt Peak Power Zener Transient Voltage Suppressors

# SOT-23 Dual Common Anode Zeners for ESD Protection

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

#### **Features**

- Pb-Free Packages are Available
- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range 3 V to 26 V
- Standard Zener Breakdown Voltage Range 5.6 V to 33 V
- Peak Power 24 or 40 Watts @ 1.0 ms (Unidirectional), per Figure 5 Waveform
- ESD Rating of Class N (exceeding 16 kV) per the Human Body Model
- Maximum Clamping Voltage @ Peak Pulse Current
- Low Leakage < 5.0 μA
- Flammability Rating UL 94 V-O

### **Mechanical Characteristics**

**CASE:** Void-free, transfer-molded, thermosetting plastic case **FINISH:** Corrosion resistant finish, easily solderable

### **MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**

260°C for 10 Seconds

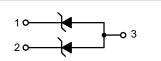
Package designed for optimal automated board assembly Small package size for high density applications Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel. Replace the "T1" with "T3" in the Device Number to order the 13 inch/10,000 unit reel.



### ON Semiconductor®

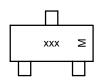
### http://onsemi.com



### MARKING DIAGRAM



SOT-23 CASE 318 STYLE 12



xxx = Device Code M = Date Code

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

### **DEVICE MARKING INFORMATION**

See specific marking information in the device marking column of the table on page 3 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit	
Peak Power Dissipation @ 1.0 ms (Note 1) MMBZ5V6ALT1 thru MMBZ10VALT1 @ T <sub>L</sub> ≤ 25°C MMBZ12VALT1 thru MMBZ33VALT1	P <sub>pk</sub>	24 40	Watts	
Total Power Dissipation on FR–5 Board (Note 2) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C	
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	556	°C/W	
Total Power Dissipation on Alumina Substrate (Note 3) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C	
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	417	°C/W	
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +150	°C	
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. Non-repetitive current pulse per Figure 5 and derate above  $T_A = 25^{\circ}C$  per Figure 6.
- 2.  $FR-5 = 1.0 \times 0.75 \times 0.62$  in.
- 3. Alumina =  $0.4 \times 0.3 \times 0.024$  in, 99.5% alumina.

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
MMBZ5V6ALT1	SOT-23	3000 Tape & Reel		
MMBZ5V6ALT1G	SOT-23 (Pb-Free)	3000 Tape & Reel		
MMBZ5V6ALT3	SOT-23	10,000 Tape & Reel		
MMBZ5V6ALT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel		
MMBZ6VxALT1	SOT-23	3000 Tape & Reel		
MMBZ6VxALT1G	SOT-23 (Pb-Free)	3000 Tape & Reel		
MMBZ6VxALT3	SOT-23	10,000 Tape & Reel		
MMBZ6VxALT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel		
MMBZ9V1ALT1	SOT-23	3000 Tape & Reel		
MMBZ9V1ALT1G	SOT-23 (Pb-Free)	3000 Tape & Reel		
MMBZ9V1ALT3	SOT-23	10,000 Tape & Reel		
MMBZ9V1ALT13G	SOT-23 (Pb-Free)	10,000 Tape & Reel		
MMBZxxVALT1	SOT-23	3000 Tape & Reel		
MBZxxVALT1G SOT-23 (Pb-Free)		3000 Tape & Reel		
MMBZxxVALT3	SOT-23	10,000 Tape & Reel		
MMBZxxVALT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

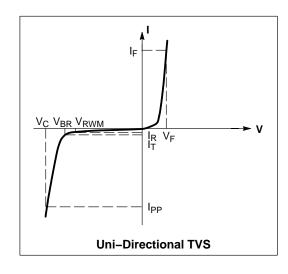
<sup>\*</sup>Other voltages may be available upon request.

### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
ΘV <sub>BR</sub>	Maximum Temperature Coefficient of V <sub>BR</sub>
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
Z <sub>ZT</sub>	Maximum Zener Impedance @ I <sub>ZT</sub>
I <sub>ZK</sub>	Reverse Current
Z <sub>ZK</sub>	Maximum Zener Impedance @ I <sub>ZK</sub>



### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA})$ 

**24 WATTS** 

				Breakdown Voltage			Max Zener Impedance (Note 5)			V <sub>C</sub> @ I <sub>PP</sub> (Note 6)			
	Device	V <sub>RWM</sub>	I <sub>R</sub> @ V <sub>RWM</sub>	V <sub>B</sub>	R (Note 4)	(V)	@ <b>ተ</b>	Z <sub>ZT</sub> @ I <sub>ZT</sub>	Z <sub>ZK</sub> (	@ l <sub>ZK</sub>	v <sub>c</sub>	I <sub>PP</sub>	$\Theta V_{BR}$
Device	Marking	Volts	μΑ	Min	Nom	Max	mA	Ω	Ω	mA	٧	Α	mV/°C
MMBZ5V6AL	5A6	3.0	5.0	5.32	5.6	5.88	20	11	1600	0.25	8.0	3.0	1.26
MMBZ6V2AL	6A2	3.0	0.5	5.89	6.2	6.51	1.0	_	-	_	8.7	2.76	2.80
MMBZ6V8AL	6A8	4.5	0.5	6.46	6.8	7.14	1.0	-	-	-	9.6	2.5	3.4
MMBZ9V1AL	9A1	6.0	0.3	8.65	9.1	9.56	1.0	_	_	_	14	1.7	7.5
MMBZ10VAL	10A	6.5	0.3	9.50	10	10.5	1.0	_	-	_	14.2	1.7	7.5

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA})$ 

### **40 WATTS**

			I <sub>R</sub> @	Breakdown Voltage			V <sub>C</sub> @ I <sub>PP</sub>								
	Device	V <sub>RWM</sub>	V <sub>RWM</sub>	V <sub>BR</sub> (Note 4) (V)		V <sub>BR</sub> (Note 4) (V)		V <sub>BR</sub> (Note 4) (V)		V <sub>BR</sub> (Note 4) <b>(V)</b> @ <b>I</b> <sub>T</sub>		V <sub>C</sub>	I <sub>PP</sub>	$\Theta V_{BR}$	
Device	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C					
MMBZ12VAL	12A	8.5	200	11.40	12	12.60	1.0	17	2.35	7.5					
MMBZ15VAL	15A	12	50	14.25	15	15.75	1.0	21	1.9	12.3					
MMBZ18VAL	18A	14.5	50	17.10	18	18.90	1.0	25	1.6	15.3					
MMBZ20VAL	20A	17	50	19.00	20	21.00	1.0	28	1.4	17.2					
MMBZ27VAL	27A	22	50	25.65	27	28.35	1.0	40	1.0	24.3					
MMBZ33VAL	33A	26	50	31.35	33	34.65	1.0	46	0.87	30.4					

V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.
 Z<sub>ZT</sub> and Z<sub>ZK</sub> are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for I<sub>Z(AC)</sub> = 0.1 I<sub>Z(DC)</sub>, with the AC frequency = 1.0 kHz.
 Surge current waveform per Figure 5 and derate per Figure 6

### **TYPICAL CHARACTERISTICS**

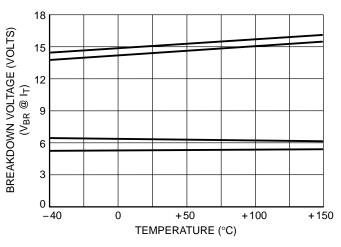


Figure 1. Typical Breakdown Voltage versus Temperature

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

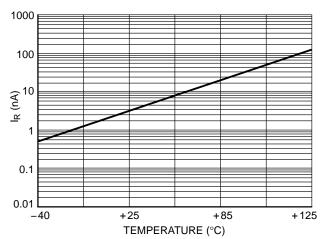


Figure 2. Typical Leakage Current versus Temperature

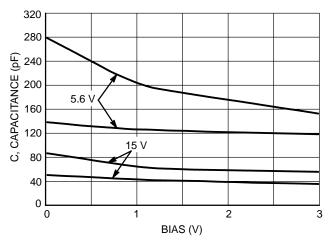


Figure 3. Typical Capacitance versus Bias Voltage
(Upper curve for each voltage is unidirectional mode,
lower curve is bidirectional mode)

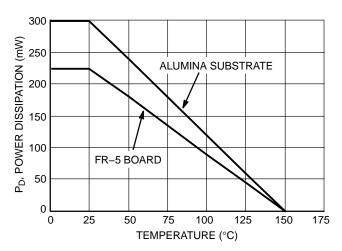
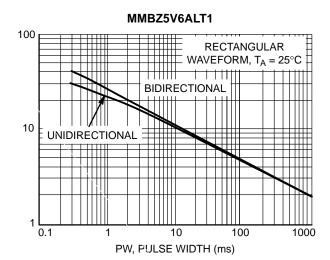
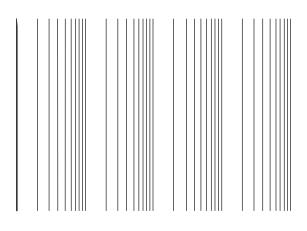


Figure 4. Steady State Power Derating Curve

### **TYPICAL CHARACTERISTICS**





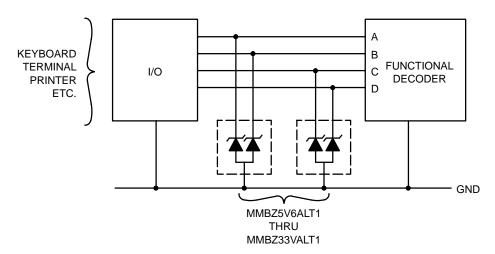
Power is defined as  $V_{RSM}\,x\,I_Z(pk)$  where  $V_{RSM}$  is the clamping voltage at  $I_Z(pk).$ 

### **TYPICAL COMMON ANODE APPLICATIONS**

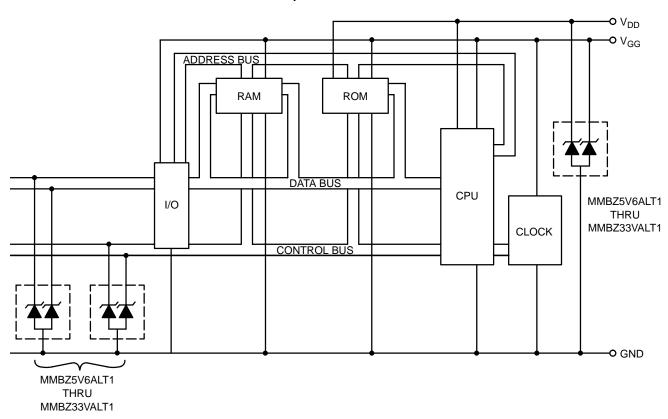
A quad junction common anode design in a SOT-23 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of TVS applications are illustrated below.

### **Computer Interface Protection**

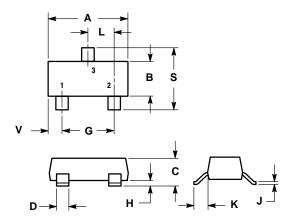


### **Microprocessor Protection**



### **PACKAGE DIMENSIONS**

SOT-23 (TO-236) CASE 318-09 ISSUE AH



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIUMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318–01, –02, AND –06 OBSOLETE, NEW STANDARD 318–09.

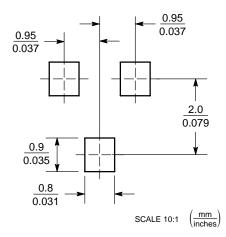
	INC	HES	MILLIMETERS				
DIM	MIN	MAX	MIN	MAX			
Α	0.1102	0.1197	2.80	3.04			
В	0.0472	0.0551	1.20	1.40			
С	0.0385	0.0498	0.99	1.26			
D	0.0140	0.0200	0.36	0.50			
G	0.0670	0.0826	1.70	2.10			
Н	0.0040	0.0098	0.10	0.25			
J	0.0034	0.0070	0.085	0.177			
K	0.0180	0.0236	0.45	0.60			
L	0.0350	0.0401	0.89	1.02			
S	0.0830	0.0984	2.10	2.50			
V	0.0177	0.0236	0.45	0.60			

### STYLE 12:

PIN 1. CATHODE 2. CATHODE

- 3. ANODE

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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